



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **Koji NOZAKI et al.**

Group Art Unit: **1752**

Application Number: **10/623,679**

Examiner: **Amanda C. Walke**

Filed: **July 22, 2003**

Confirmation Number: **5083**

For: **RESIST PATTERN THICKENING MATERIAL, RESIST PATTERN
AND PROCESS FOR FORMING THE SAME, AND
SEMICONDUCTOR DEVICE AND PROCESS FOR
MANUFACTURING THE SAME**

Attorney Docket Number: **030891**
Customer Number: **38834**

INFORMATION DISCLOSURE STATEMENT
UNDER 37 C.F.R. 1.97(c)(2)

Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

July 6, 2007

Sir:

Applicants direct the attention of the Patent and Trademark Office to the documents listed on the attached PTO/SB/08. A copy of each non- U.S. document is attached.

This Information Disclosure Statement is being submitted after issuance of a first official action on the merits and expiration of the three month period following the filing date or the entry of the national stage for the above-captioned application, but prior to issuance of either a final official action or a Notice of Allowance. A check is attached hereto which covers the **\$180.00** fee set forth in 37 C.F.R. §1.17(p).

07/09/2007 AWONDAF1 00000069 10623679

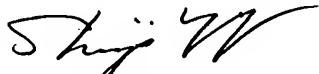
02 FC:1806

180.00 0P

Information Disclosure Statement under 1.97(c)(2)
Attorney Docket No. 030891
Serial No. 10/623,679

If there are any fees due in connection with the filing of this paper, please charge Deposit
Account No. 50-2866.

Respectfully submitted,
WESTERMAN, HATTORI, DANIELS & ADRIAN, LLP



Shuji Yoshizaki
Attorney for Applicants
Registration No. L0111
Telephone: (202) 822-1100
Facsimile: (202) 822-1111

SY/mt
Enclosures: Limited Recognition
PTO/SB/08
3 Documents
Check for \$180.00



**BEFORE THE OFFICE OF ENROLLMENT AND DISCIPLINE
UNITED STATES PATENT AND TRADEMARK OFFICE**

LIMITED RECOGNITION UNDER 37 CFR § 11.9(b)

Shuji Yoshizaki is hereby given limited recognition under 37 CFR §11.9(b) as an employee of Westerman Hattori Daniels & Adrian, LLP, to prepare and prosecute patent applications wherein the patent applicant is the client of Westerman Hattori Daniels & Adrian, LLP, and the attorney or agent of record in the applications is a registered practitioner who is a member of Westerman Hattori Daniels & Adrian, LLP. This limited recognition shall expire on the date appearing below, or when whichever of the following events first occurs prior to the date appearing below: (i) Shuji Yoshizaki ceases to lawfully reside in the United States, (ii) Shuji Yoshizaki's employment with Westerman Hattori Daniels & Adrian, LLP ceases or is terminated, or (iii) Shuji Yoshizaki ceases to remain or reside in the United States on an H-1B visa.

This document constitutes proof of such recognition. The original of this document is on file in the Office of Enrollment and Discipline of the U.S. Patent and Trademark Office.

**Limited Recognition No. L0111.
Expires: July 7, 2010**



Harry I. Moatz
Director of Enrollment and Discipline



Combined Form PTO/SB/08A&B  INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				<i>Complete if Known</i>	
Sheet	1	of	1	Application Number	10/623,679
				Confirmation Number	5083
				Filing Date	July 22, 2003
				First Named Inventor	Koji NOZAKI et al.
				Art Unit	1752
				Examiner Name	Amanda C. Walke
				Attorney Docket Number	030891

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 1

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶
	1	Takeo Ishibashi et al.; Advanced Micro-Lithography Process with Chemical Shrink Technology; The Japan Society of Applied Physics; Japanese Journal of Applied Physics, Vol. 40 (2001), January 15, 2001, pp. 419-425;	
	2	Mamoru Terai et al.; Below 70-nm Contact Hole Pattern with RELACS Process on ArF Resist; Advances in Resist Technology and Processing XX, Theodore H. Fedynyshyn, Editor; Proceedings of SPIE Vol. 5039 (2003), June 12, 2003	
	3	Mamoru Terai et al.; Newly Developed Resolution Enhancement Lithography Assisted by Chemical Shrink Process and Materials for Next-Generation Devices; The Japan Society of Applied Physics; Japanese Journal of Applied Physics, Vol. 45, No. 6B (2006), June 20, 2006, pp. 5354-5358	

Examiner Signature		Date Considered	
--------------------	--	-----------------	--

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or in the comment box of this document. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to indicate here if English language Translation is attached.